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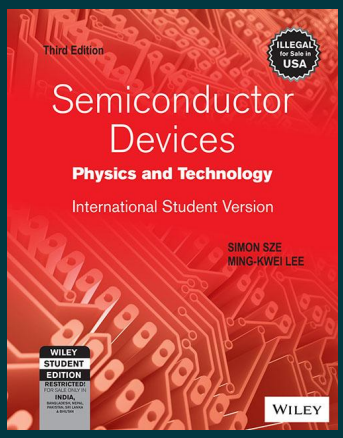


# Semiconductor Devices, Physics and Technology, 3ed, ISV

By Simon Sze, Ming-Kwei Lee

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## Description

This book is an introduction to the physical principles of modern semiconductor devices and their advanced fabrication technology. It begins with a brief historical review of major devices and key technologies and is then divided into three sections: semiconductor material properties, physics of semiconductor devices and processing technology to fabricate these semiconductor devices.

## About the Author

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